DATA SHEET

PHOTOCOUPLER PS2581L1,PS2581L2

LONG CREEPAGE TYPE HIGH ISOLATION VOLTAGE 4-PIN PHOTOCOUPLER

-NEPOC Series-

DESCRIPTION

NEC

The PS2581L1, PS2581L2 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon phototransistor in a plastic DIP (Dual In-line Package).

Creepage distance and clearance of leads are over 8 millimeters.

The PS2581L2 is lead bending type (Gull-wing) for surface mounting.

FEATURES

- Long creepage and clearance distance (8 mm)
- High isolation voltage (BV = 5 000 Vr.m.s.)
- High collector to emitter voltage (VCEO = 80 V)
- High-speed switching (tr = 3 μ s TYP., tr = 5 μ s TYP.)
- High current transfer ratio (CTR = 200 % TYP.)
- UL approved: File No. E72422 (S)
- CSA approved: No. CA101391
- BSI approved: No. 8243/8244
- NEMKO approved: No. P97103006
- DEMKO approved: No. 307269
- SEMKO approved: No. 9741154/01
- FIMKO approved: No. 018277
- VDE0884 approved

ORDERING INFORMATION

Part Number	Package	Safety Standard Approval	Application Part Number [™]
PS2581L1	4-pin DIP	UL, CSA, BSI, NEMKO, DEMKO,	PS2581L1
PS2581L2	4-pin DIP (lead bending surface mount)	SEMKO, FIMKO, VDE approved	PS2581L2
PS2581L2-E3, E4	4-pin DIP taping		

*1 As applying to Safety Standard, following part number should be used.

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PHOTOCOUPLER CONSTRUCTION

Parameter	Unit (MIN.)
Air Distance	8 mm
Outer Creepage Distance	8 mm
Inner Creepage Distance	4 mm
Isolation Distance	0.4 mm

Parameter		Symbol	Ratings	Unit
Diode	Forward Current (DC)	lf	80	mA
	Reverse Voltage	VR	6	V
	Power Dissipation Derating	$\Delta P_D / ^{\circ}C$	1.5	mW/°C
	Power Dissipation		150	mW
Peak Forward Current ^{*1}		IFP	1	А
Transistor	Collector to Emitter Voltage	Vceo	80	V
	Emitter to Collector Voltage	Veco	7	V
	Collector Current	lc	50	mA
	Power Dissipation Derating	⊿Pc/°C	1.5	mW/°C
	Power Dissipation	Pc	150	mW
Isolation Voltage ²		BV	5 000	Vr.m.s.
Operating Ambient Temperature		TA	–55 to +100	°C
Storage Temperature		Tstg	–55 to +150	°C

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

*1 PW = 100 μ s, Duty Cycle = 1 %

*2 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS (TA = 25 °C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Diode	Forward Voltage	VF	IF = 10 mA		1.17	1.4	V
	Reverse Current	R	Vr = 5 V			5	μA
	Terminal Capacitance	Ct	V = 0 V, f = 1.0 MHz		50		pF
Transistor	Collector to Emitter Dark Current	ICEO	Vce = 80 V, IF = 0 mA			100	nA
Coupled	Current Transfer Ratio (Ic/IF)*1	CTR	IF = 5 mA, VCE = 5 V	80	200	400	%
	Collector Saturation Voltage	Vce(sat)	IF = 10 mA, Ic = 2 mA			0.3	V
	Isolation Resistance	Ri-o	VI-0 = 1.0 kVDC	10 ¹¹			Ω
	Isolation Capacitance	CI-0	V = 0 V, f = 1.0 MHz		0.5		pF
	Rise Time ^{⁺₂}	tr	Vcc = 10 V, Ic = 2 mA,		3		μs
	Fall Time ^{*2}	tr	RL = 100 Ω		5		

*1 CTR rank

- L : 200 to 400 (%)
- M: 80 to 240 (%)
- D : 100 to 300 (%)
- H : 80 to 160 (%)
- W : 130 to 260 (%)
- N : 80 to 400 (%)

*2 Test circuit for switching time





TYPICAL CHARACTERISTICS (TA = 25 °C, unless otherwise specified)







COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



COLLECTOR CURRENT vs. COLLECTOR SATURATION VOLTAGE



10

50

ts

tr td

TYP.

10⁵

50 k 100 k



Remark The graphs indicate nominal characteristics.

***** TAPING SPECIFICATIONS (in millimeters)



***** NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

- Peak reflow temperature
- Time of peak reflow temperature
- Time of temperature higher than 220°C
- Time to preheat temperature from 120 to 180°C
- Number of reflows
- Flux

260°C or below (package surface temperature) 10 seconds or less 60 seconds or less 120±30 s Three

Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



Time (s)

(2) Wave soldering

- Temperature 260°C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(3) Cautions

• Fluxes

Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output or between collector-emitters at startup, the output side may enter the on state, even if the voltage is within the absolute maximum ratings.

★ USAGE CAUTIONS

- 1. Protect against static electricity when handling.
- 2. Avoid storage at a high temperature and high humidity.

★

SPECIFICATION OF VDE MARKS LICENSE DOCUMENT (VDE0884)

Parameter	Symbol	Speck	Unit
Application classification (DIN VDE 0109)			
for rated line voltages \leq 300 Vr.m.s.		IV	
for rated line voltages \leq 600 Vr.m.s.		III	
Climatic test class (DIN IEC 68 Teil 1/09.80)		55/100/21	
Dielectric strength maximum operating isolation voltage.	UIORM	890	V _{peak}
Test voltage (partial discharge test procedure a for type test and random test)	Upr	1 068	Vpeak
$U_{pr} = 1.2 \times U_{IORM}, P_d < 5 pC$			
Test voltage (partial discharge test procedure b for all devices test)	Upr	1 424	Vpeak
$U_{pr} = 1.6 \times U_{IORM}, P_d < 5 pC$			
Highest permissible overvoltage	Utr	8 000	V_{peak}
Degree of pollution (DIN VDE 0109)		2	
Clearance distance		> 8.0	mm
Creepage distance		> 8.0	mm
Comparative tracking index (DIN IEC 112/VDE 0303 part 1)	CTI	175	
Material group (DIN VDE 0109)		lll a	
Storage temperature range	Tstg	–55 to +150	°C
Operating temperature range	TA	–55 to +100	°C
Isolation resistance, minimum value			
V _I o = 500 V dc at T _A = 25 °C	Ris MIN.	10 ¹²	Ω
V_{IO} = 500 V dc at TA MAX. at least 100 °C	Ris MIN.	10 ¹¹	Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal			
derating curve)			
Package temperature	Tsi	175	°C
Current (input current IF, Psi = 0)	lsi	400	mA
Power (output or total power dissipation)	Psi	700	mW
Isolation resistance			
Vio = 500 V dc at TA = 175 °C (Tsi)	Ris MIN.	10 ⁹	Ω

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M8E 00.4-0110

SAFETY INFORMATION ON THIS PRODUCT

Caution GaAs Products	The product contains gallium arsenide, GaAs. GaAs vapor and powder are hazardous to human health if inhaled or ingested.		
	Do not destroy or burn the product.		
 Do not cut or cleave off any part of the product. 			
 Do not crush or chemically dissolve the product. 			
 Do not put the product in the mouth. 			
	Follow related laws and ordinances for disposal. The product should be excluded from general industrial waste or household garbage.		

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